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June 2014

FDMC86102L

N-Channel Shielded Gate PowerTrench $^{\otimes}$ MOSFET 100 V, 18 A, 23 m Ω

Features

- Shielded Gate MOSFET Technology
- Max $r_{DS(on)} = 23 \text{ m}\Omega$ at $V_{GS} = 10 \text{ V}$, $I_D = 7 \text{ A}$
- Max $r_{DS(on)}$ = 34 m Ω at V_{GS} = 4.5 V, I_D = 5.5 A
- Low Profile 1 mm max in Power 33
- RoHS Compliant



General Description

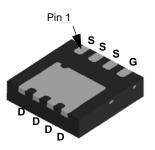
This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench® process that incorporates Shielded Gate technology. This process has been optimized for the on-state resistance and yet maintain superior switching performance.

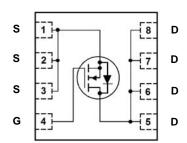
Application

■ DC - DC Conversion

Top Bottom







MLP 3.3x3.3

MOSFET Maximum Ratings T_A = 25 °C unless otherwise noted

Symbol	Parameter			Ratings	Units
V _{DS}	Drain to Source Voltage			100	V
V _{GS}	Gate to Source Voltage			±20	V
	Drain Current -Continuous	T _C = 25 °C		18	
I_D	-Continuous	T _A = 25 °C	(Note 1a)	7	Α
	-Pulsed			30	
E _{AS}	Single Pulse Avalanche Energy		(Note 3)	63	mJ
D	Power Dissipation	T _C = 25 °C		41	W
P_D	Power Dissipation	T _A = 25 °C	(Note 1a)	2.3	VV
T _{.I} , T _{STG}	Operating and Storage Junction Tempera	ature Range		-55 to +150	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	53	C/VV

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMC86102L	FDMC86102L	Power 33	13 "	12 mm	3000 units

Electrical Characteristics $T_J = 25 \, ^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Chara	octeristics					
BV _{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$	100			V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	I_D = 250 μ A, referenced to 25 °C		71		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 80 V, V _{GS} = 0 V			1	μΑ
I _{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$			±100	nA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	1	1.8	3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250 \mu A$, referenced to 25 °C		-6		mV/°C
		$V_{GS} = 10 \text{ V}, I_D = 7 \text{ A}$		18.9	23	
r _{DS(on)}	r _{DS(on)} Static Drain to Source On Resistance	$V_{GS} = 4.5 \text{ V}, I_D = 5.5 \text{ A}$		24.9	34	mΩ
	$V_{GS} = 10 \text{ V}, I_D = 7 \text{ A}, T_J = 125 ^{\circ}\text{C}$		31.9	39	1	
9 _{FS}	Forward Transconductance	$V_{DS} = 5 \text{ V}, I_{D} = 7 \text{ A}$		26		S

Dynamic Characteristics

C _{iss}	Input Capacitance	V 50 V V 0 V	999	1330	pF
C _{oss}	Output Capacitance	$V_{DS} = 50 \text{ V}, V_{GS} = 0 \text{ V},$ $f = 1 \text{ MHz}$	178	240	pF
C _{rss}	Reverse Transfer Capacitance	1 - 1 1/11/12	7.6	15	pF
R_g	Gate Resistance		0.5		Ω

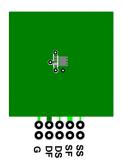
Switching Characteristics

t _{d(on)}	Turn-On Delay Time		7.7	16	ns
t _r	Rise Time	$V_{DD} = 50 \text{ V}, I_D = 7 \text{ A},$	2.2	10	ns
t _{d(off)}	Turn-Off Delay Time	V_{GS} = 10 V, R_{GEN} = 6 Ω	19	34	ns
t _f	Fall Time		2.4	10	ns
$Q_{g(TOT)}$	Total Gate Charge	V _{GS} = 0 V to 10 V	15	22	nC
$Q_{g(TOT)}$	Total Gate Charge	$V_{GS} = 0 \text{ V to } 4.5 \text{ V}$ $V_{DD} = 50 \text{ V},$ $I_{D} = 7 \text{ A}$	7.3	11	nC
Q_{gs}	Total Gate Charge	1 _D = 7 A	2.7		nC
Q_{gd}	Gate to Drain "Miller" Charge		2.3		nC

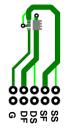
Drain-Source Diode Characteristics

Ved Source to Drain Dioge Forward Voltage	Source to Drain Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{S} = 7 \text{ A}$	(Note 2)		0.81	1.3	V
	$V_{GS} = 0 \text{ V}, I_{S} = 2 \text{ A}$	(Note 2)		0.74	1.2	V	
t _{rr}	Reverse Recovery Time	I _F = 7 A, di/dt = 100 A/μs			45	72	ns
Q _{rr}	Reverse Recovery Charge			45	72	nC	

^{1.} R_{BJA} is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. R_{BJC} is guaranteed by design while R_{BCA} is determined by the user's board design.



a) 53 °C/W when mounted on a 1 in² pad of 2 oz copper



b) 125 °C/W when mounted on a minimum pad of 2 oz copper

- 2. Pulse Test: Pulse Width < 300 $\mu\text{s},$ Duty cycle < 2.0%.
- 3. Starting T $_J$ = 25 °C; N-ch: L = 1 mH, I $_{AS}$ = 11.3 A, V $_{DD}$ = 90 V, V $_{GS}$ = 10 V.

Typical Characteristics T_J = 25 °C unless otherwise noted

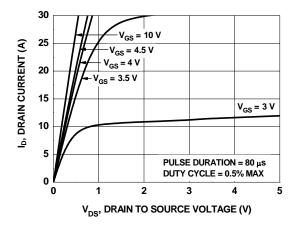


Figure 1. On Region Characteristics

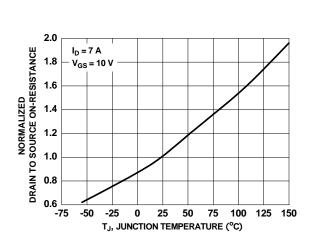


Figure 3. Normalized On Resistance vs. Junction Temperature

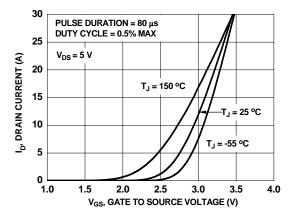


Figure 5. Transfer Characteristics

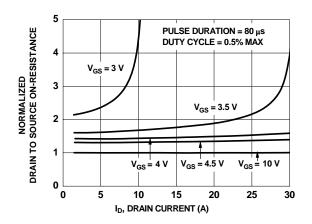


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

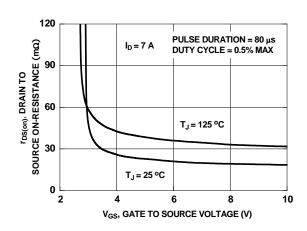


Figure 4. On-Resistance vs. Gate to Source Voltage

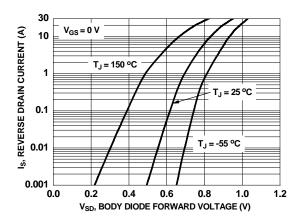


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

Typical Characteristics $T_J = 25$ °C unless otherwise noted

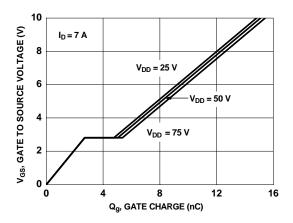


Figure 7. Gate Charge Characteristics

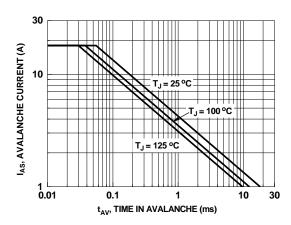


Figure 9. Unclamped Inductive Switching Capability

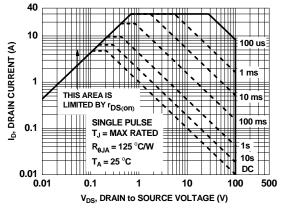


Figure 11. Forward Bias Safe Operating Area

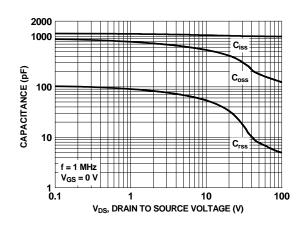


Figure 8. Capacitance vs. Drain to Source Voltage

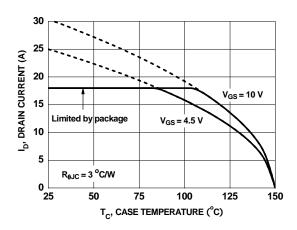


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

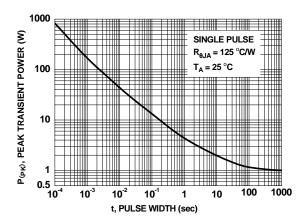


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics $T_J = 25$ °C unless otherwise noted

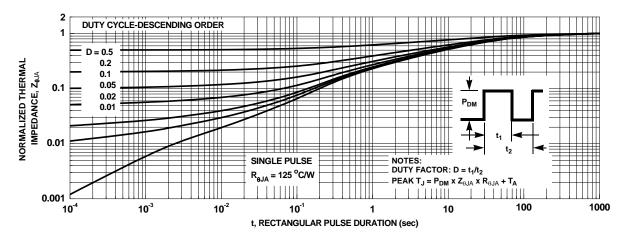
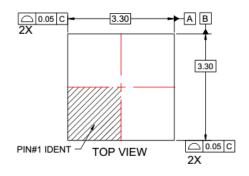
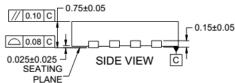
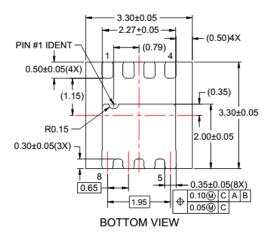


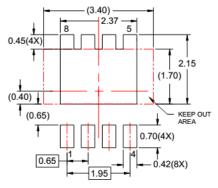
Figure 13. Junction-to-Ambient Transient Thermal Response Curve

Dimensional Outline and Pad Layout









RECOMMENDED LAND PATTERN

NOTES:

- A. DOES NOT CONFORM TO JEDEC REGISTRATION MO-229
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.
- D. LAND PATTERN RECOMMENDATION IS EXISTING INDUSTRY LAND PATTERN.
- E. DRAWING FILENAME: MKT-MLP08Srev3.



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